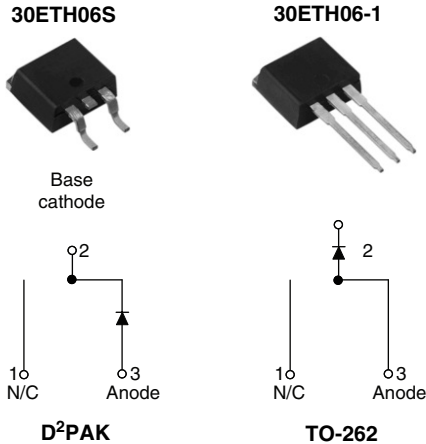


## Hyperfast Rectifier, 30 A FRED Pt™



### FEATURES

- Hyperfast recovery time
- Low forward voltage drop
- Low leakage current
- 125 °C operating junction temperature
- Dual diode center tap
- Designed and qualified for industrial level

### DESCRIPTION/APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC-DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

### PRODUCT SUMMARY

$t_{rr}$ (typical)	28 ns
$I_{F(AV)}$	30 A
$V_R$	600 V

### ABSOLUTE MAXIMUM RATINGS

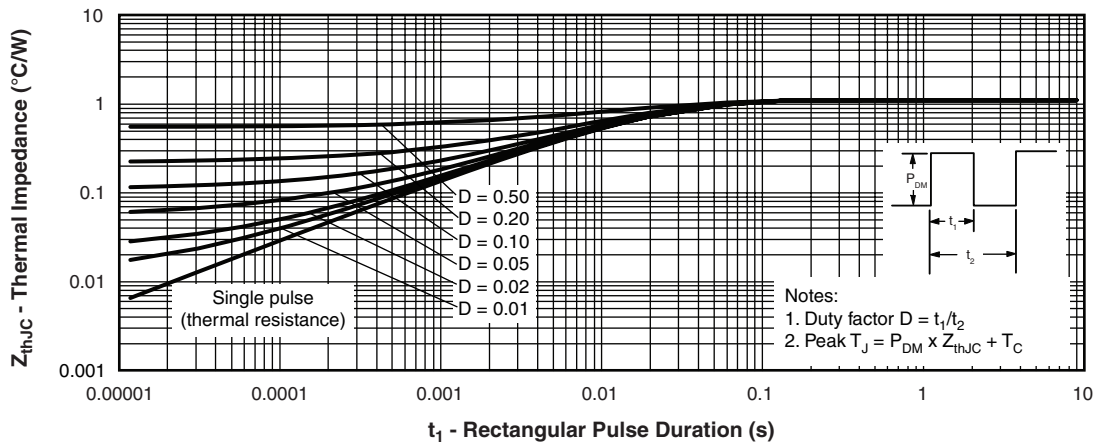
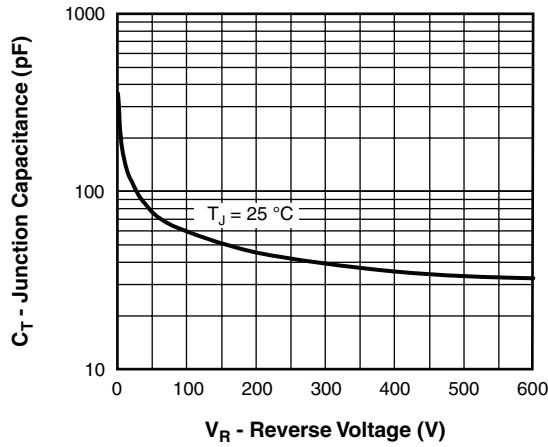
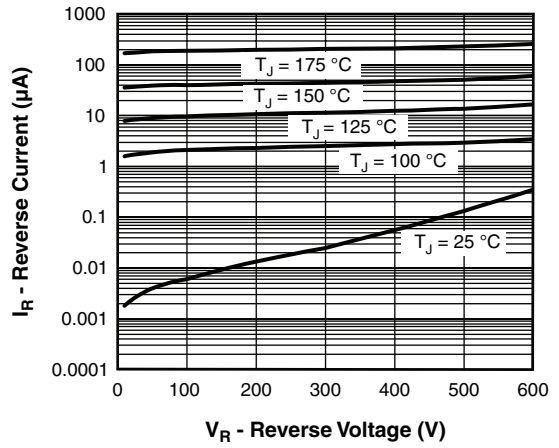
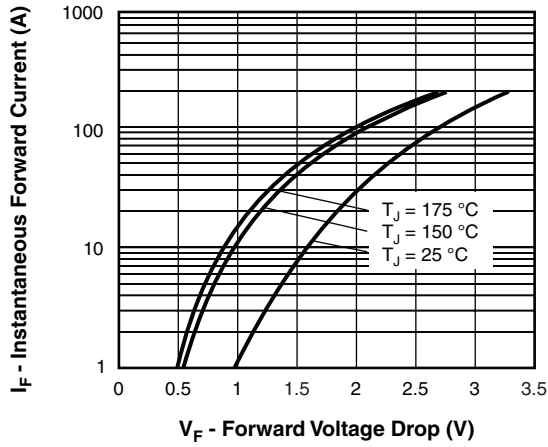
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Peak repetitive reverse voltage	$V_{RRM}$		600	V
Average rectified forward current	$I_{F(AV)}$	$T_C = 103\text{ °C}$	30	A
Non-repetitive peak surge current	$I_{FSM}$	$T_J = 25\text{ °C}$	200	
Operating junction and storage temperatures	$T_J, T_{Stg}$		- 65 to 175	°C

### ELECTRICAL SPECIFICATIONS ( $T_J = 25\text{ °C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	$V_{BR}, V_R$	$I_R = 100\ \mu\text{A}$	600	-	-	V
Forward voltage	$V_F$	$I_F = 30\text{ A}$	-	2.0	2.6	
		$I_F = 30\text{ A}, T_J = 150\text{ °C}$	-	1.34	1.75	
Reverse leakage current	$I_R$	$V_R = V_R\text{ rated}$	-	0.3	50	$\mu\text{A}$
		$T_J = 150\text{ °C}, V_R = V_R\text{ rated}$	-	60	500	
Junction capacitance	$C_T$	$V_R = 600\text{ V}$	-	33	-	pF
Series inductance	$L_S$	Measured lead to lead 5 mm from package body	-	8.0	-	nH

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Reverse recovery time	$t_{rr}$	$I_F = 1.0\text{ A}$ , $di_F/dt = 50\text{ A}/\mu\text{s}$ , $V_R = 30\text{ V}$	-	28	35	ns	
		$T_J = 25\text{ }^\circ\text{C}$	-	31	-		
		$T_J = 125\text{ }^\circ\text{C}$	-	77	-		
Peak recovery current	$I_{RRM}$	$I_F = 30\text{ A}$ $di_F/dt = 200\text{ A}/\mu\text{s}$ $V_R = 200\text{ V}$	$T_J = 25\text{ }^\circ\text{C}$	-	3.5	-	A
			$T_J = 125\text{ }^\circ\text{C}$	-	7.7	-	
Reverse recovery charge	$Q_{rr}$	$I_F = 30\text{ A}$ $di_F/dt = 200\text{ A}/\mu\text{s}$ $V_R = 200\text{ V}$	$T_J = 25\text{ }^\circ\text{C}$	-	65	-	nC
			$T_J = 125\text{ }^\circ\text{C}$	-	345	-	

<b>THERMAL - MECHANICAL SPECIFICATIONS</b>						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	$T_J, T_{Stg}$		- 65	-	175	$^\circ\text{C}$
Thermal resistance, junction to case per leg	$R_{thJC}$		-	0.7	1.1	$^\circ\text{C}/\text{W}$
Thermal resistance, junction to ambient per leg	$R_{thJA}$	Typical socket mount	-	-	70	
Thermal resistance, case to heatsink	$R_{thCS}$	Mounting surface, flat, smooth and greased	-	0.2	-	
Weight			-	2.0	-	g
			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style D <sup>2</sup> PAK	30ETH06S			
		Case style TO-262	30ETH06-1			



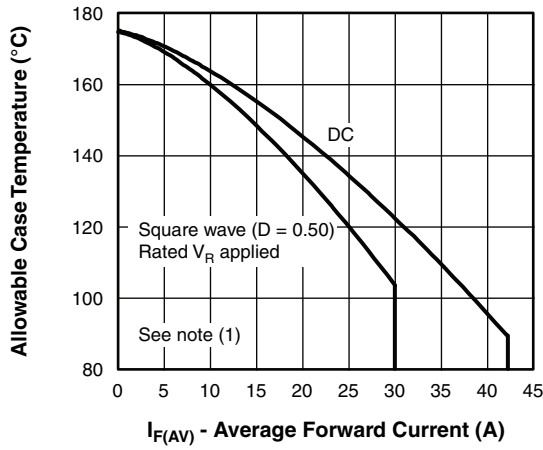


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

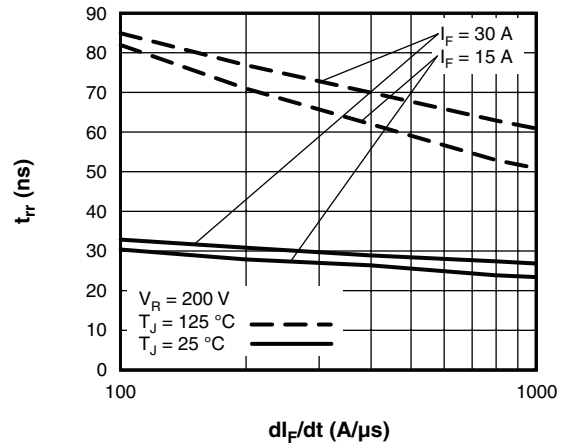


Fig. 7 - Typical Reverse Recovery Time vs.  $di_F/dt$

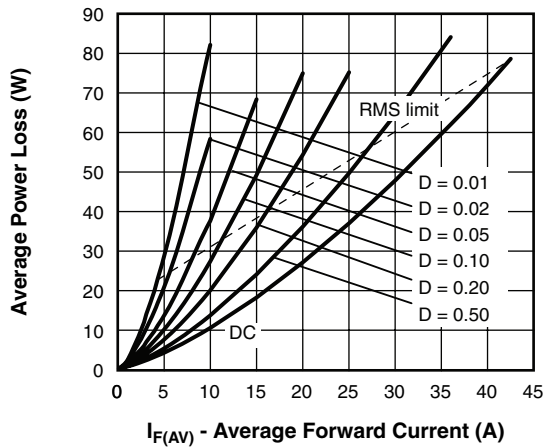


Fig. 6 - Forward Power Loss Characteristics

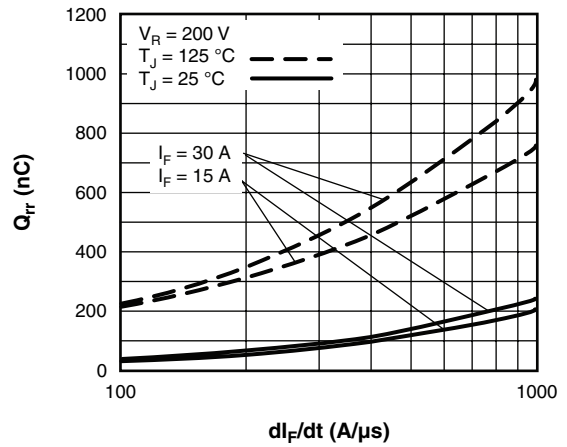


Fig. 8 - Typical Stored Charge vs.  $di_F/dt$

**Note**

- (1) Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;  
 $Pd$  = Forward power loss =  $I_{F(AV)} \times V_{FM}$  at  $(I_{F(AV)}/D)$  (see fig. 6);  
 $Pd_{REV}$  = Inverse power loss =  $V_{R1} \times I_R (1 - D)$ ;  $I_R$  at  $V_{R1}$  = Rated  $V_R$

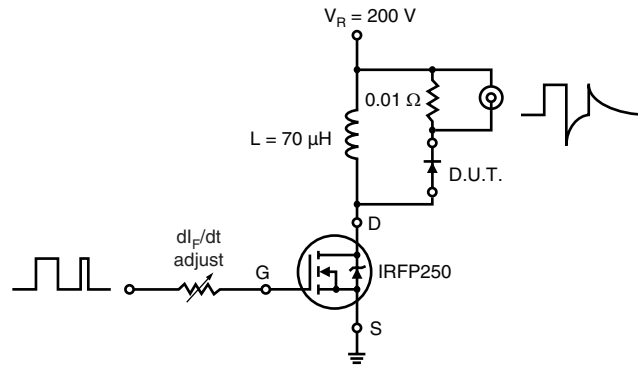
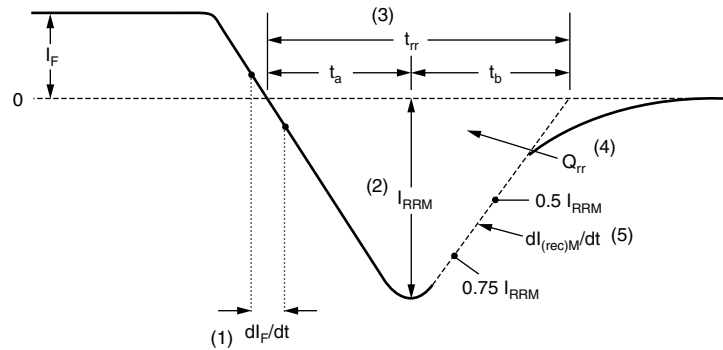


Fig. 9 - Reverse Recovery Parameter Test Circuit



- |   |   |
|---|---|
| <p>(1) <math>dl_F/dt</math> - rate of change of current through zero crossing</p> <p>(2) <math>I_{RRM}</math> - peak reverse recovery current</p> <p>(3) <math>t_{rr}</math> - reverse recovery time measured from zero crossing point of negative going <math>I_F</math> to point where a line passing through <math>0.75 I_{RRM}</math> and <math>0.50 I_{RRM}</math> extrapolated to zero current.</p> | <p>(4) <math>Q_{rr}</math> - area under curve defined by <math>t_{rr}</math> and <math>I_{RRM}</math></p> $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$ <p>(5) <math>dl_{(rec)M}/dt</math> - peak rate of change of current during <math>t_b</math> portion of <math>t_{rr}</math></p> |
|---|---|

Fig. 10 - Reverse Recovery Waveform and Definitions



## ORDERING INFORMATION TABLE

Device code	<b>30</b>	<b>E</b>	<b>T</b>	<b>H</b>	<b>06</b>	<b>S</b>	<b>TRL</b>	<b>-</b>
	①	②	③	④	⑤	⑥	⑦	⑧

- 1** - Current rating (30 = 30 A)
- 2** - E = Single diode
- 3** - T = TO-220, D<sup>2</sup>PAK
- 4** - H = Hyperfast recovery
- 5** - Voltage rating (06 = 600 V)
- 6** -
  - S = D<sup>2</sup>PAK
  - -1 = TO-262
- 7** -
  - None = Tube (50 pieces)
  - TRL = Tape and reel (left oriented, for D<sup>2</sup>PAK package)
  - TRR = Tape and reel (right oriented, for D<sup>2</sup>PAK package)
- 8** -
  - None = Standard production
  - PbF = Lead (Pb)-free

LINKS TO RELATED DOCUMENTS	
Dimensions	<a href="http://www.vishay.com/doc?95014">http://www.vishay.com/doc?95014</a>
Part marking information	<a href="http://www.vishay.com/doc?95008">http://www.vishay.com/doc?95008</a>
Packaging information	<a href="http://www.vishay.com/doc?95032">http://www.vishay.com/doc?95032</a>



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